

PNP Transistor

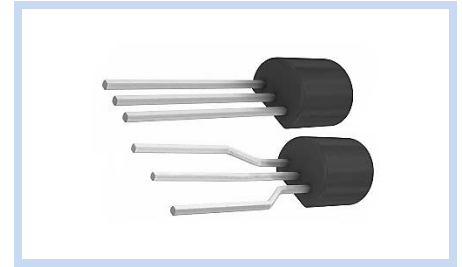
80V 625mW TO-92

MPSA56

MERITEK

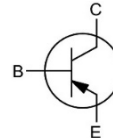
FEATURE

- Collector-emitter Voltage $V_{CE}=-80V$
- Collector current: -500mA
- Application: Signal Processing, Switching, Amplification



MECHANICAL DATA

- Case: TO-92, molded plastic
- Terminals: Solderable per MIL-STD-750, Method 2026



MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-4.0	V
Collector Continuous Current	I_C	-500	mA
Power Dissipation	P_D	625	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 ~ +150	°C

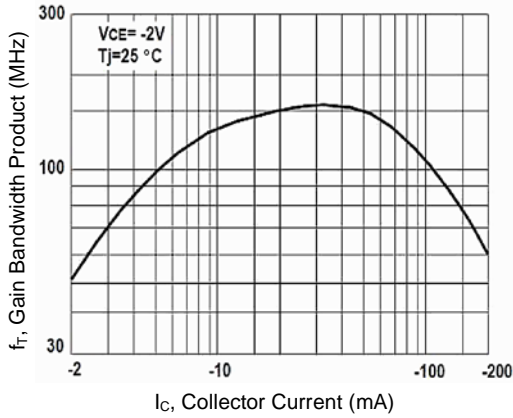
ELECTRICAL CHARACTERISTICS

Parameter	Conditions	Symbol	Min.	Max.	Unit
DC Current Gain	$V_{CE}=-1V, I_C=-10mA$	h_{FE}	100	-	-
	$V_{CE}=-1V, I_C=-100mA$		100	-	
Collector Base Cutoff Current	$V_{CB}=-80V$	I_{CBO}	-	-100	nA
Collector Emitter Cutoff Current	$V_{CE}=-60V$	I_{CES}	-	-100	nA
Collector Base Breakdown Voltage	$I_C=-1mA$	$V_{(BR)CBO}$	-80	-	V
Emitter Base Breakdown Voltage	$I_E=-100\mu A$	$V_{(BR)EBO}$	-4.0	-	V
Collector Emitter Saturation Voltage	$I_C=-100mA, I_B=-10mA$	$V_{CE(sat)}$	-	-0.25	V
Base Emitter Saturation Voltage	$V_{CE}=-1V, I_C=-100mA$	$V_{BE(on)}$	-	-1.20	V
Transition Frequency at 100MHz	$V_{CE}=-2V, I_C=-10mA$	f_T	50	-	MHz

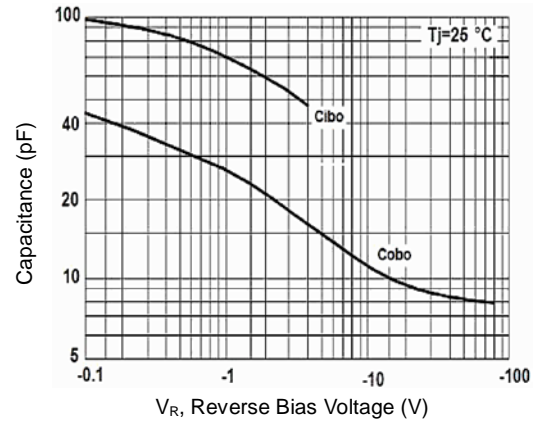
Note: $T_A=25^\circ C$, unless otherwise noted.

CHARACTERISTIC CURVES

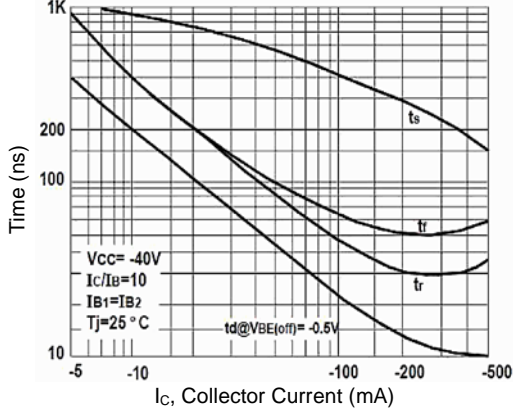
Gain Bandwidth Product



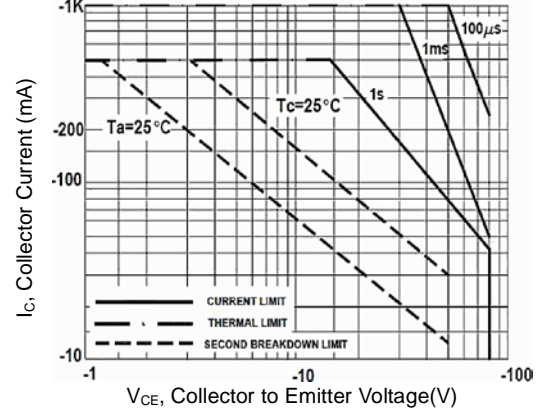
Capacitance



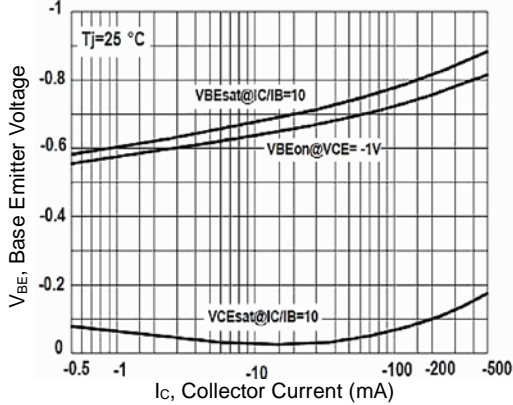
Switching Time



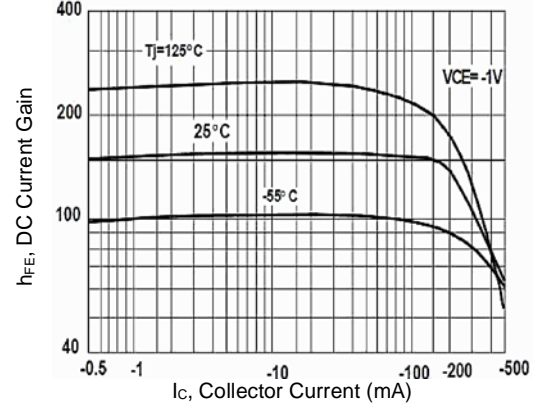
Maximum Safe Operating Area



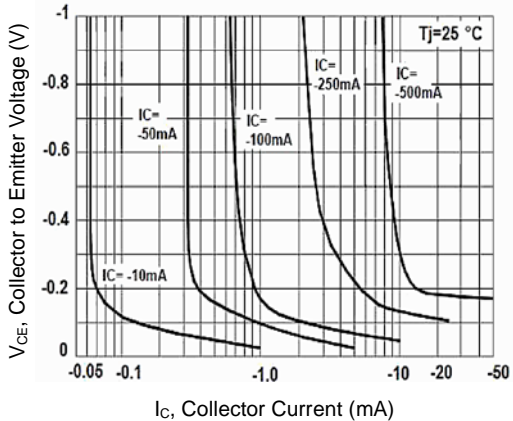
Base Emitter On Voltage



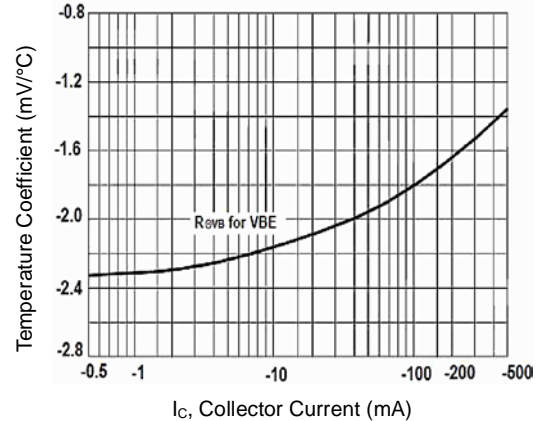
DC Current Gain



Collector Saturation Region



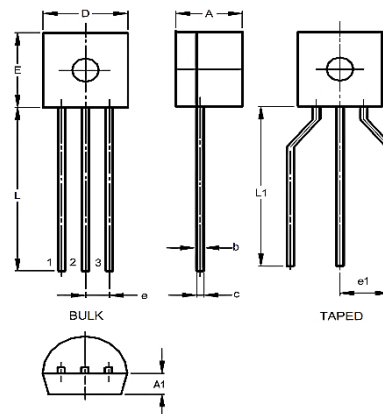
Base Emitter Temperature Coefficient



DIMENSIONS

Unit: mm

TO-92	Min	Max
A	3.50	3.70
A1	1.00	1.20
b	0.35	0.45
c	0.29	0.39
D	4.50	4.70
e	1.17	1.37
e1	2.44	2.94
E	4.50	4.70
L	12.50	--
L1	12.00	--



PACKING OPTIONS

Part NO.	Package	Packing Code	Type	Packing
MPSA56	TO-92	TA	Bent Lead	Tape & Reel Ammo
		B	Straight Lead	Bulk